

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|---------------------------------------------------------------------------|--------------------------------|---------------------|
| 1 | 144 | isolation with silicon adj carbide | USPAT; EPO; JPO; DERWENT | 2004/08/19 11:29 |
| 2 | 0 | isolation with (silicon adj carbide) and insulat\$3 near2 conductivity | USPAT; EPO; JPO; DERWENT | 2004/08/19 11:29 |
| 3 | 144 | isolation with (silicon adj carbide) | USPAT; EPO; JPO; DERWENT | 2004/08/19 11:30 |
| 4 | 29 | (isolation with (silicon adj carbide)) and MOSFET | USPAT; EPO; JPO; DERWENT | 2004/08/19 11:30 |